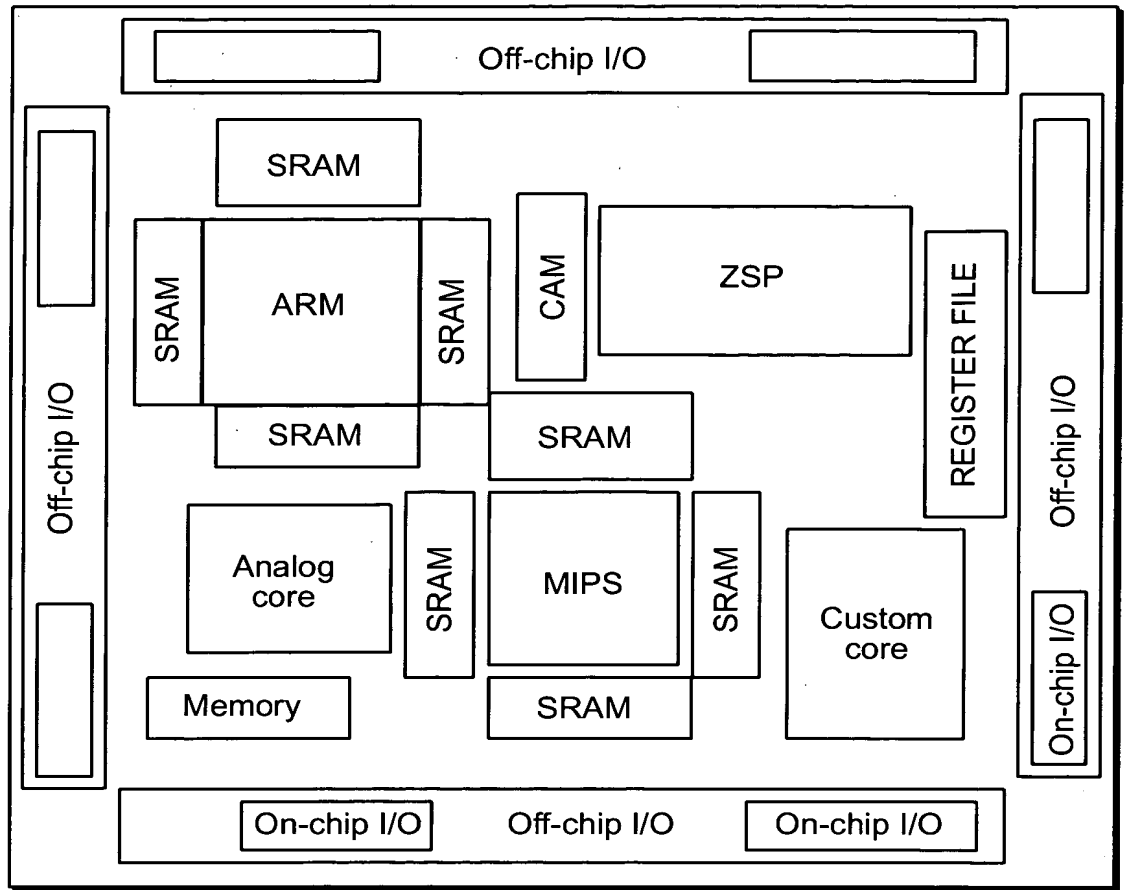
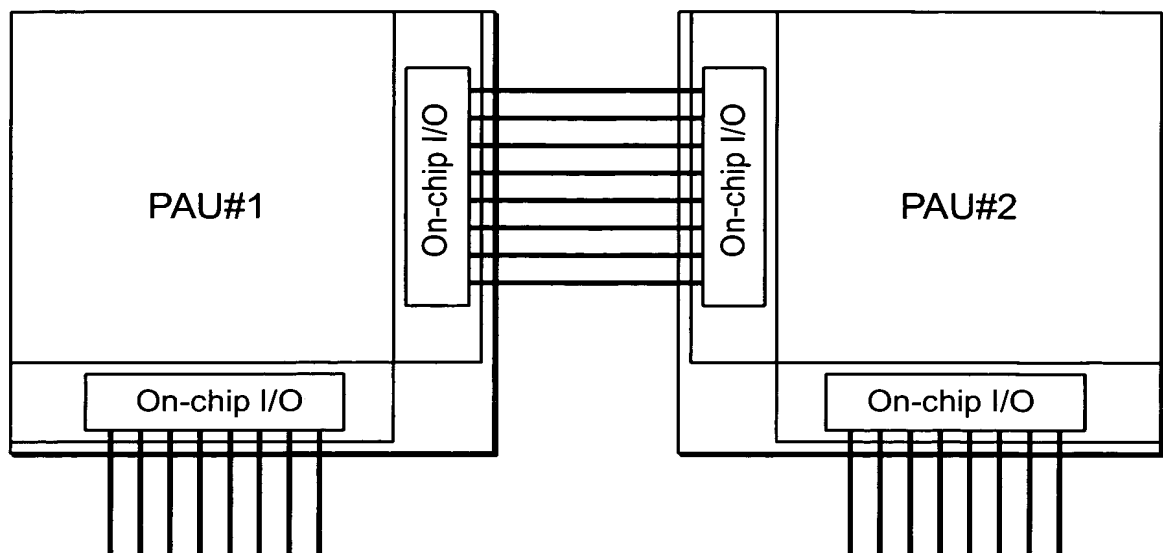
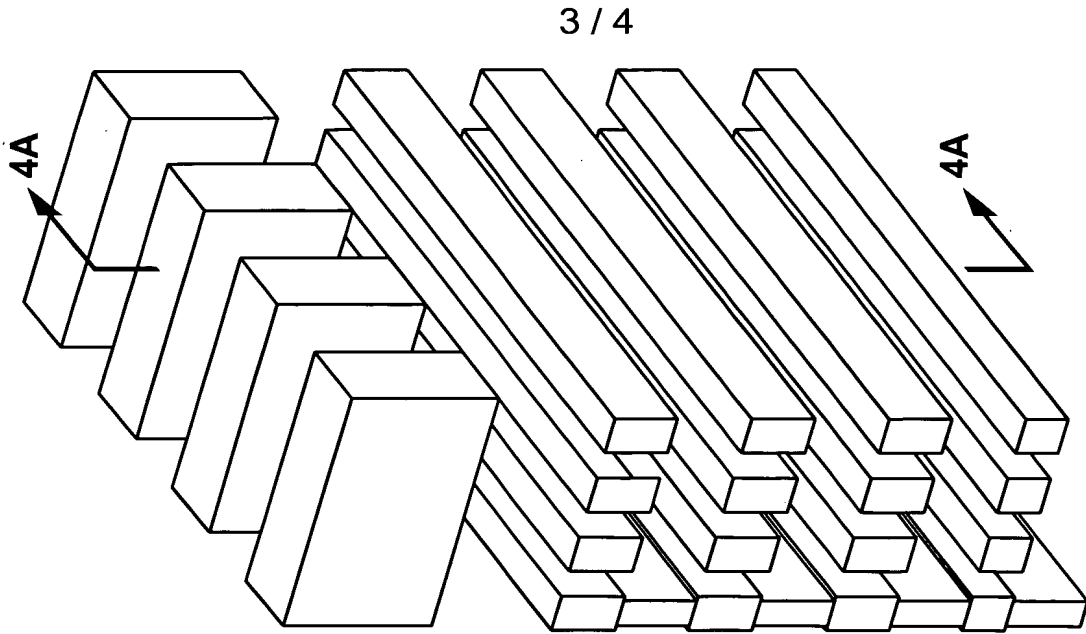
**FIG.\_1**

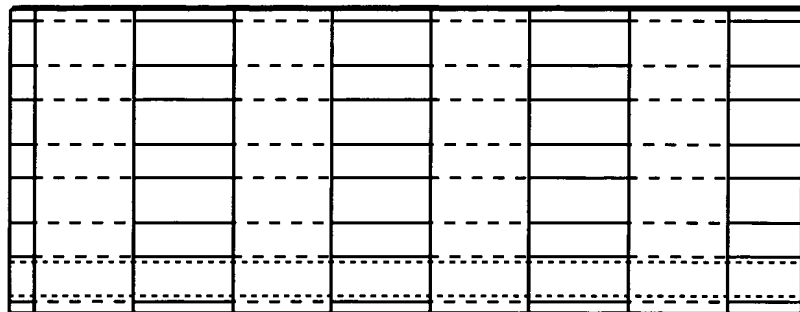
**FIG. 2**

200

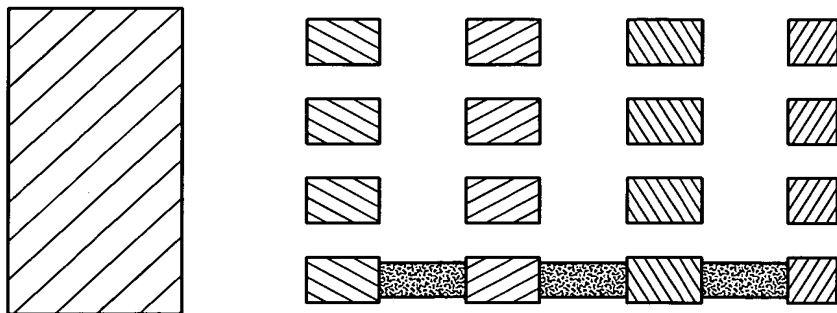
**FIG. 3**



**FIG.\_4C**



**FIG.\_4B**

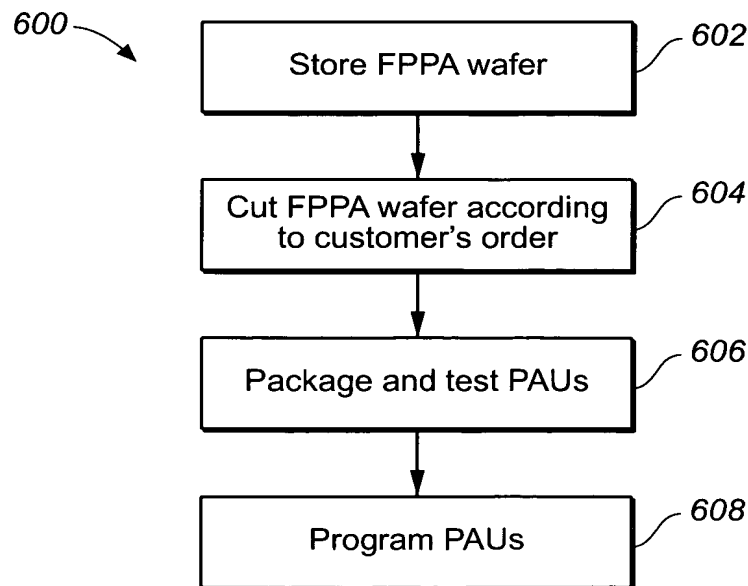


**FIG.\_4A**

### Interconnect Layer Comparison

Layer	Advantages (+)	Disadvantages (-)
<b>Bumping metal Cu</b>	R very low; Units testable; Die seal not compromised; Unlimited array size;	Tied to flip chip; Lines wide;
<b>Pad Metal Al</b>	R low; Non low K; Laser programmable;	Array size limit; Smear; No unit test;
<b>Within IC Cu</b>	Fine line; Multi-layer	Die seal integrity; Array size limit; No unit test;
<b>Poly</b>	Fine line; Robust; No smear;	High R; Array size limit; No unit test;
<b>Silicon</b>	Medium Line; Robust; Minimal qualification needed;	Very high R; Repair difficult; Array size limit; No unit test;

**FIG.\_5**



**FIG.\_6**